

GENERAL DESCRIPTION

DP8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

PRODUCT SUMMARY

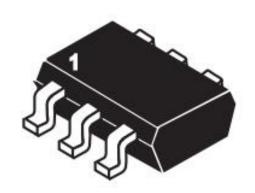
 V_{DS} 20 V

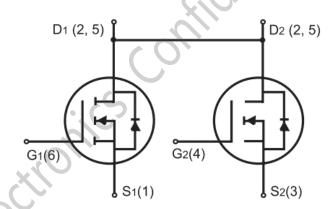
 I_D (at V_{GS} =4.5V) 5.0A

 $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 29m Ω

 $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) < 34m Ω

SOT23-6





Absolute Maximum	Ratings	T∆=25°C	unless	otherwise	noted
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Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous @ T _J =25°C	I _D	5	Α
Pulsed ^b	I _{DM}	20	А
Drain-Sourse Diode Forward Current ^a	I _S	2.5	Α
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Parameter	Symbol	Limit	Unit
Thermal Resistance, Junction-to-Ambient ^a	$R_{\theta JA}$	100	°C/W
Thermal Resistance, Junction to Lead	$R_{ heta_{JL}}$	65	°C/W



ELECTRICAL CHARACTERISTICS (TA=25°Cunless otherwise noted)

Symbol	Condition	Min	Typ ^c	Max	Unit		
Off Characteristics							
BV _{DSS}	V_{GS} =0V I_D =250 μ A	20	-	-	V		
I _{DSS}	$V_{DS}=20V,V_{GS}=0V$	ı	-	1	μΑ		
I _{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$	ı	-	±100	nA		
On Characteristics							
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.5	0.7	1.2	V		
	V _{GS} =4.5V, I _D =4.5A	14	20	29	mΩ		
K _{DS(ON)}	V_{GS} =2.5V, I_{D} =3.5A	17	27	34	mΩ		
g _{FS}	$V_{DS}=5V,I_{D}=7A$	-	17.7	-	S		
Dynamic Characteristics							
C _{lss}	$V_{DS}=8V$	ı	802	-	pF		
C _{oss}	V_{GS} =0 V ,	1	153	-	рF		
C _{rss}	F=1.0MHz	ı	122	-	pF		
Switching Characteristics							
t _{d(on)}	V _{DD} =10V,	-	18	-	nS		
t	I _D =1A	-	5	-	nS		
t _{d(off)}		-	43.8	-	nS		
t _f	$R_L=10\Omega$	-	20	-	nS		
Q_g	V _{DS} =10V,	-	10.5	-	nC		
Q_{gs}	I _D =4A,	-	2	-	nC		
Q_{gd}	V _{GS} =4.5V	-	2.5	-	nC		
Drain-Source Diode Characteristics							
V _{SD}	V _{GS} =0V,I _S =1.7A	-	-	1.2	V		
	BV _{DSS} I _{DSS} I _{DSS} V _{GS(th)} R _{DS(ON)} GFS C _{Iss} C _{oss} C _{rss} t _{d(on)} t _r t _{d(off)} t _f Q _g Q _{gs} Q _{gd}	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		

Notes:

- a. Surface Mounted on FR4 Board ,T<10 sec;
- b. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- c. Guaranteed by Design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

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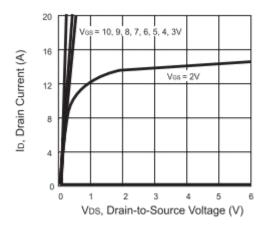


Figure 1. Output Characteristics

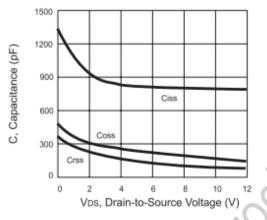


Figure 3. Capacitance

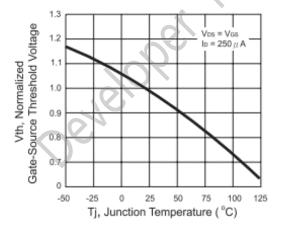


Figure 5. Gate Threshold Variation with Temperature

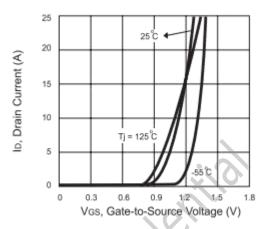


Figure 2. Thansfer Characteristics

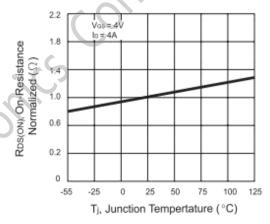


Figure 4. On-Resistance Variation with Temperature

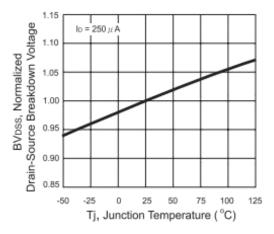


Figure 6. Breakdown Voltage Variation with Temperature



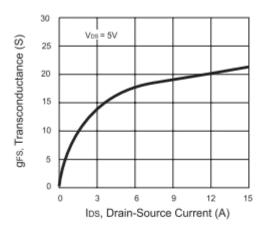


Figure 7. Transconductance Variation with Drain Current

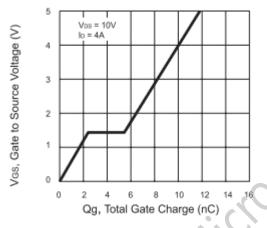


Figure 9. Gate Charge

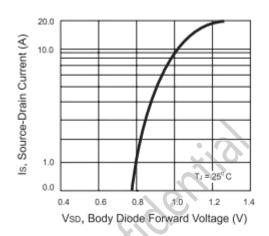


Figure 8. Body Diode Forward Voltage
Variation with Source Current

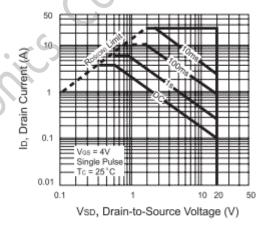


Figure 10. Maximum Safe Operating Area

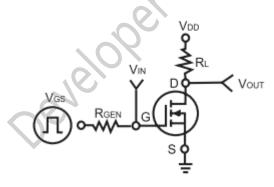


Figure 11. Switching Test Circuit

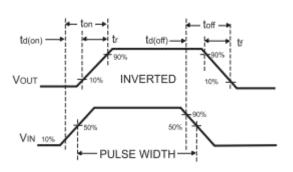


Figure 12. Switching Waveforms



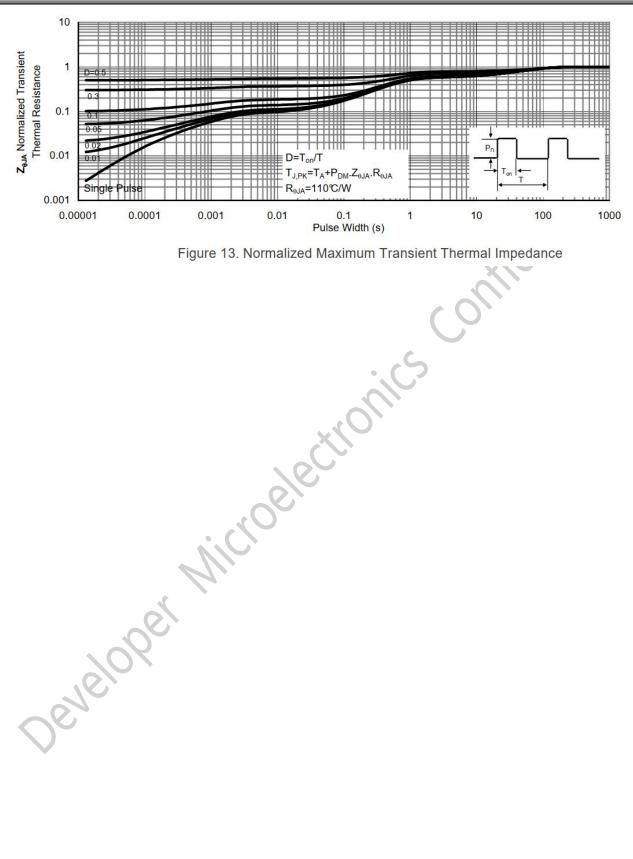
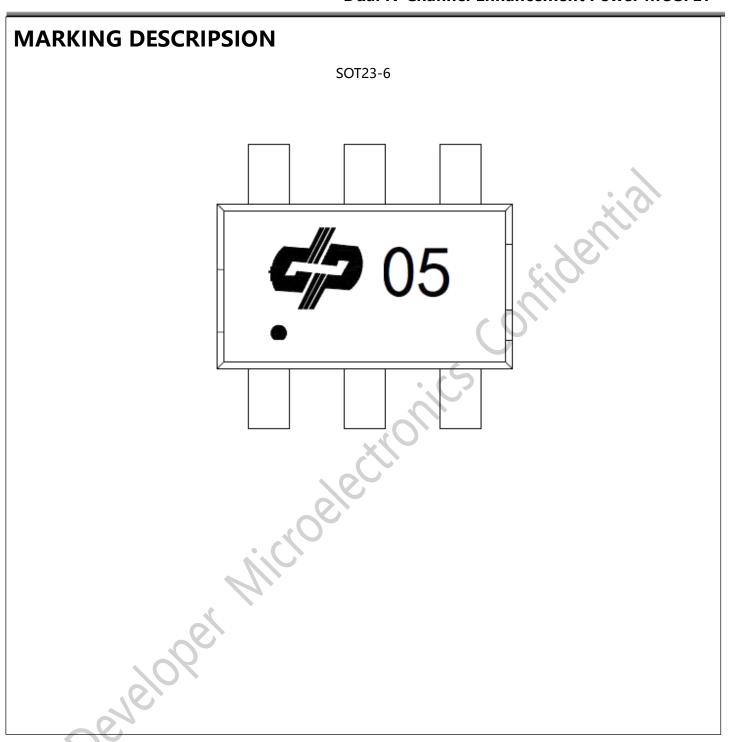


Figure 13. Normalized Maximum Transient Thermal Impedance



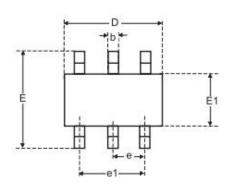


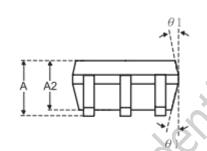


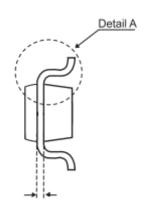


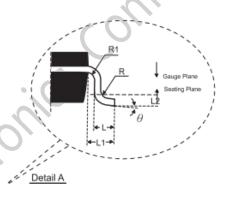
PACKAGE OUTLINE DIMENSIONS

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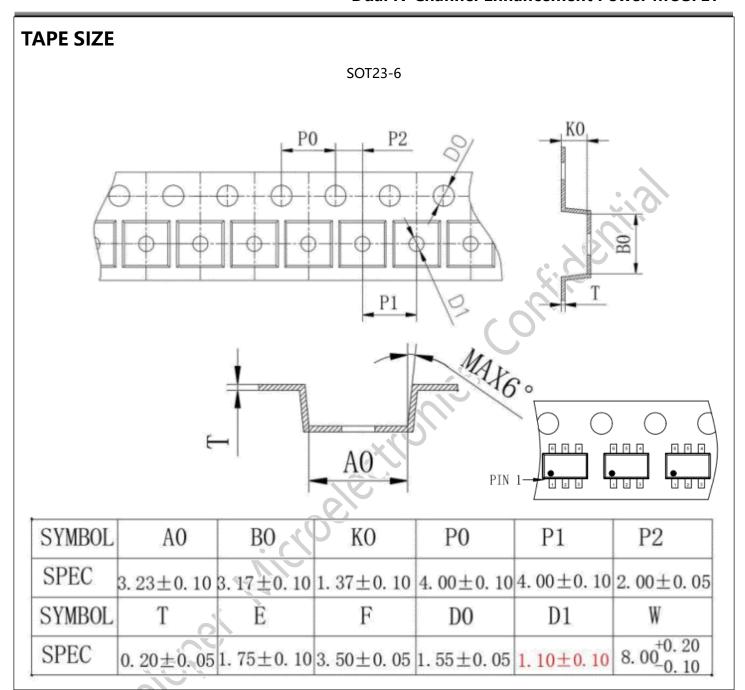




			MILLIMETERS	3	
	SYMBOLS	Win.	Nom.	Max.	
Denelobe	Α	.	-	1.45	
	A2	0.90	0.15	1.30	
	b	0.30	-	0.50	
	С	0.08	-	0.22	
	D	2.70	2.90	3.10	
	Е	2.50	2.80	3.10	
	E1	1.50	1.60	1.70	
	е	0.95 BSC			
	e1	1.90 BSC			
	L	0.30	0.45	0.60	
	L1	0.60 BSC			
	L2	0.20 BSC			
	R	0.10	-		
	R1	0.10	-	0.25	
	θ	0°	4°	8°	
	θ1	0°	10°	15°	









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